

*H.S./Helfkraut H
P. D. Wilson
1-10-02*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

ROBERTUS D.J. VERHAAR ET AL

NL 000627

Serial No.

Group Art Unit

Filed: CONCURRENTLY

Ex.

Title: METHOD OF FORMING A SEMICONDUCTOR STRUCTURE

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

A Sub C15
B. (amended) A method as claimed in claim 1, wherein a non-volatile memory cell is applied as part of the semiconductor structure, which non-volatile memory cell employs the ONO insulating layer between a floating gate and control gate thereof.

Sub C17
C. (amended) A method as claimed in claim 1, wherein the subsequent oxidation of the silicon sub-layer of the Oxide-Nitride-